Ordering number : ENA0189A

SANYO Semiconductors
DATA SHEET

N-Channel Silicon MOSFET

FSS218 — General-Purpose Switching Device Applications

Features

- Motor drive applications.
- Inverter drive applications.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		35	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		8	A
Drain Current (PW≤10s)	I_D	Duty cycle≤1%	8.5	A
Drain Current (PW≤10μs)	I_{DP}	Duty cycle≤1%	32	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (2000mm²×0.8mm), PW≤10s	1.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	35			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=35V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=10V, I_D=1mA	1.5		2.5	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=8A	5.4	9		S
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=8A, V_{GS}=10V		20	26	mΩ
	$R_{DS}(on)2$	I_D=4A, V_{GS}=4V		38	54	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		1050		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		200		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		140		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		17		ns
Rise Time	t_r	See specified Test Circuit.		65		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		75		ns
Fall Time	t_f	See specified Test Circuit.		45		ns

Marking : S218

Continued on next page.

SANYO Semiconductor Co., Ltd.
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

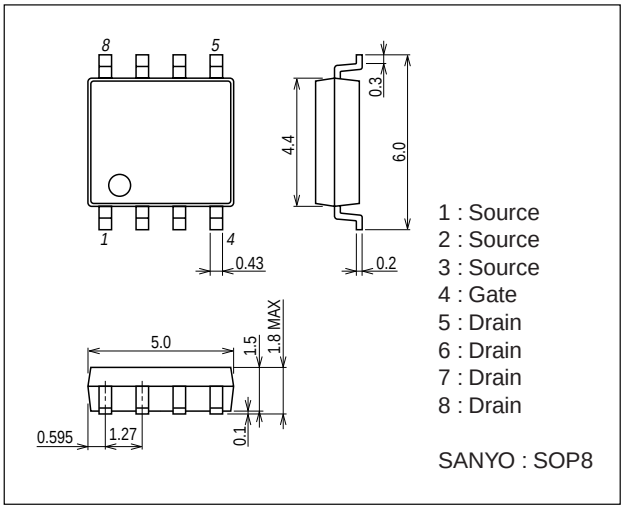
Continued from preceding page.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=8A		19		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=10V, I_D=8A		3.3		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=10V, V_{GS}=10V, I_D=8A		3.5		nC
Diode Forward Voltage	V_{SD}	I_S=8A, V_{GS}=0V		0.85	1.2	V

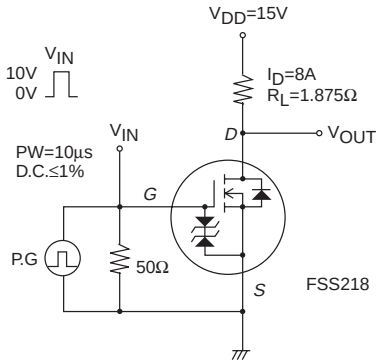
Package Dimensions

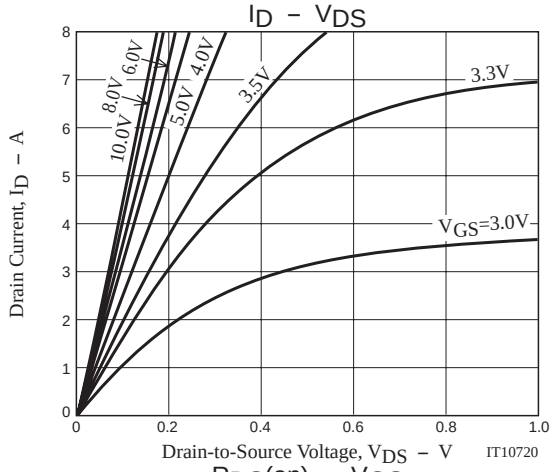
unit : mm

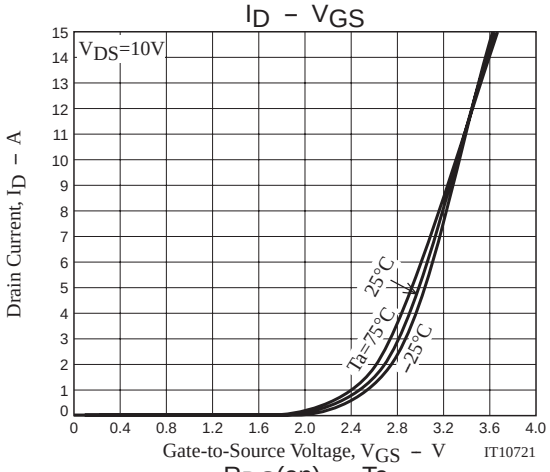
7005-002

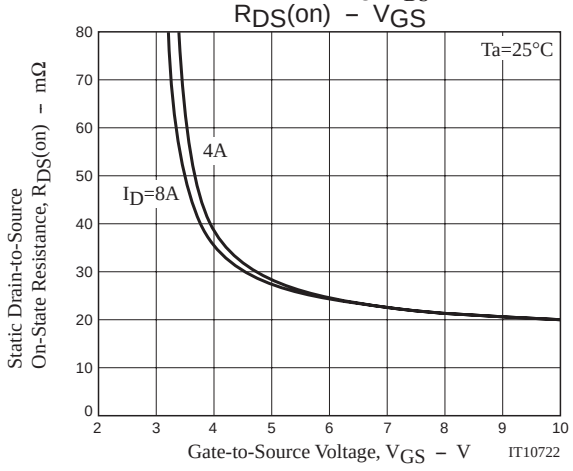


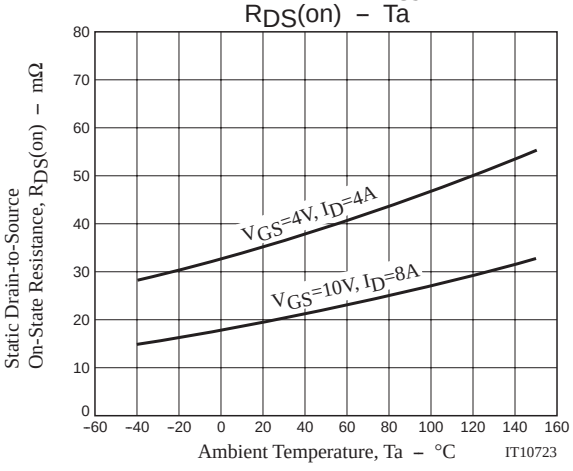
Switching Time Test Circuit

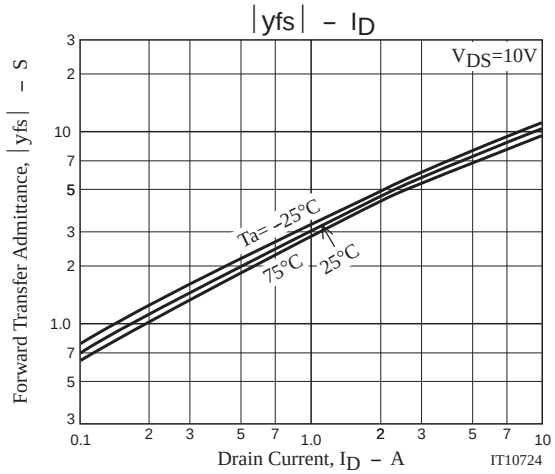


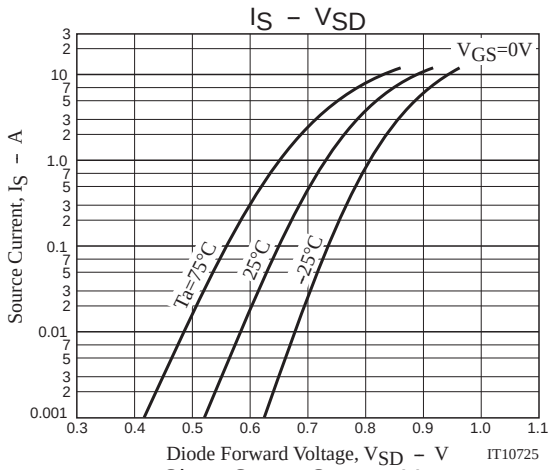


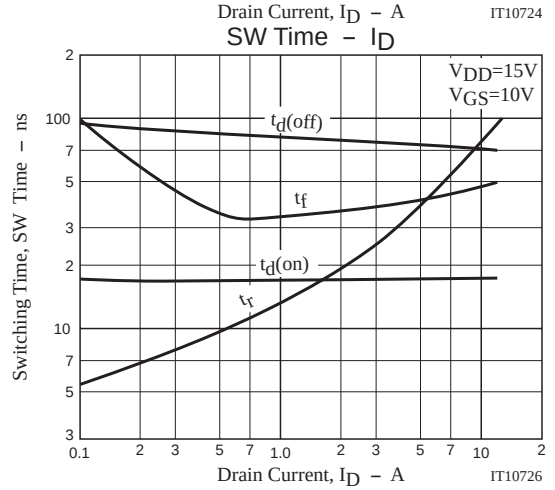


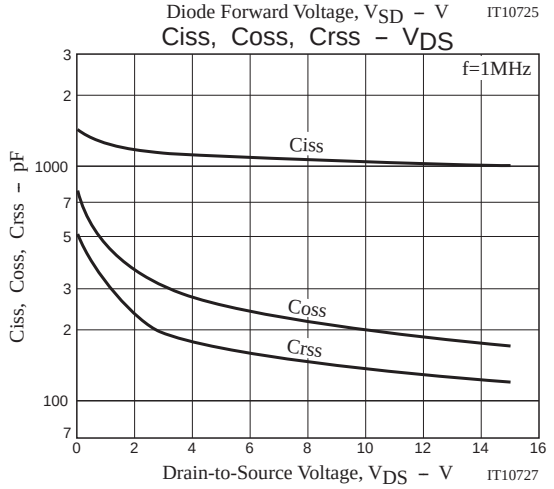


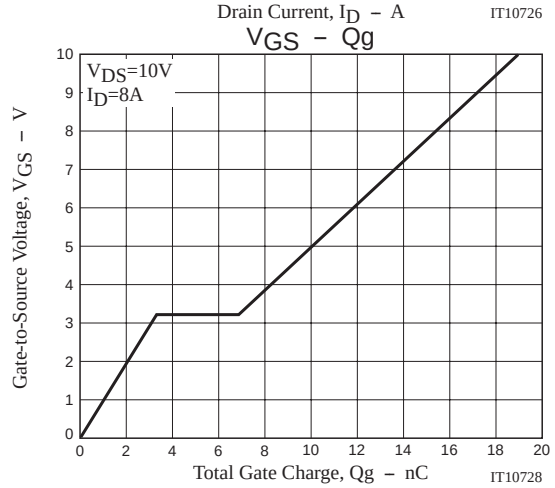


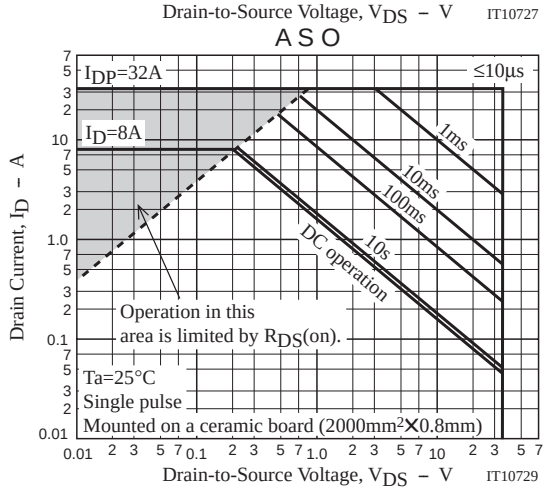


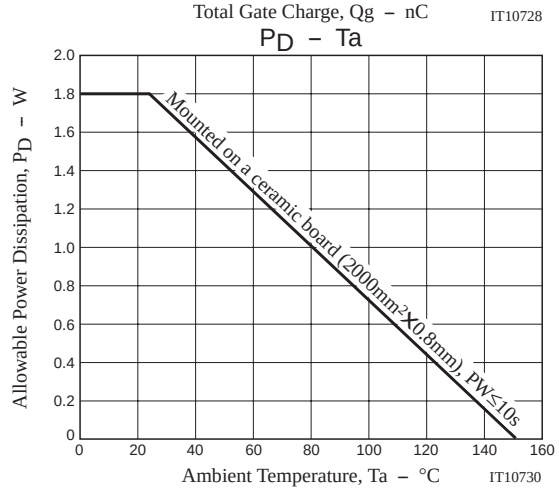












Note on usage : Since the FSS218 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of April, 2006. Specifications and information herein are subject to change without notice.